भारतीय प्रौद्योगिकी संस्थान जम्मू
INDIAN INSTITUTE OF TECHNOLOGY JAMMU

Advt. No.: IITJMU/R&C/RP-100334/A-160 **Dated: 19.01.2026**

Advertisement for the Position of Junior Research Fellow (JRF) / (कनिष्ठ अनुसंधान अध्येता)

भारतीय नागरिकों से "**Design and development of Ultraviolet detectors based on wideband gap semiconductors**" शीर्षक परियोजना (प्रायोजक: इसरो) में कनिष्ठ अनुसंधान अध्येता (JRF) के पद हेतु आवेदन आमंत्रित किए जाते हैं।

Applications are invited from interested Indian candidates for the post of Junior Research Fellow (JRF) to work on the project titled "**Design and development of Ultraviolet detectors based on wideband gap semiconductors**" sanctioned by, **ISRO**.

पदों की संख्या **No. of Positions**	पद का नाम **Position**	अनुसंधान क्षेत्र **Area of Research**	कार्यकाल **Duration**	फेलोशिप **Consolidated Salary per Month**
1 (One)	Junior Research Fellow	Microelectronics	Initially for six months. Based on the satisfactory performance, may be extendable up to 2 years	INR 37,000 + 20 % HRA

न्यूनतम शैक्षणिक योग्यता / Minimum Educational Qualification:

1. No percentage criteria will be applied for class 10th and 12th marks for all categories of application.

2. **For General/EWS/OBC Category candidates, following are required:**

   a. M.E./M. Tech or equivalent in ECE/EIE/EEE/ETC/EE or other allied branches with 60% marks or a CGPA of 6.0 on a 10.00-point scale.

   b. B.E./B.Tech. or equivalent in ECE/EIE/EEE/ETC/EE or other allied branches with 60% marks or a CGPA of 6.0 on a 10.00-point scale.

   c. A valid GATE Score for a candidate applying for Ph.D. directly after B.E./B.Tech./M.Sc.

3. For SC/ST/PH Category candidates, following are required:

   a. M.E./M. Tech or equivalent in ECE/EIE/EEE/ETC/EE or other allied branches with 55% marks or a CGPA of 5.5 on a 10.00-point scale.

   b. B.E./B.Tech. or equivalent in ECE/EIE/EEE/ETC/EE or other allied branches with 55% marks or a CGPA of 5.5 on a 10.00-point scale.

   c. A valid GATE Score for a candidate applying for Ph.D. directly after B.E./B.Tech./M.Sc.

4. Candidates submitted/defended PhD thesis in Microelectronics or allied subjects can also apply.

आयु सीमा / Age Eligibility: Maximum age: **28 years**.

- Age relaxation admissible as per Government of India rules, i.e.: 5 years for SC/ST candidates, 3 years for OBC (NCL) candidates, Women etc.

वांछनीय ज्ञान / Desirable knowledge:

1. Basic knowledge of semiconductor physics.
2. Basic knowledge of device simulation.

परियोजना का संक्षिप्त उद्देश्य / Brief Objective of Project:

- .Design and optimization of wide band-gap semiconductor (AlGaN) based UV photodetector devices with the initial help of simulation.
- Growth optimization of device layers for UV photodetector.
- Detailed material characterizations to estimate the suitability of the grown multilayer structures for device fabrication.
- Implementation of the device fabrication process flow for the photodetector.
- Electrical and optical characterizations of the fabricated photodetector to obtain the performance parameters.
- Implementation of the required modifications in the simulation, growth and fabrication steps to improve the performance parameters.
- Improvement of the device performance in terms of Dark current, Responsivity, Detectivity and and rise/fall time.

कार्य विवरण / Job Description:

The selected candidate is expected to work on

- Modeling
- Device Fabrication
- Characterizations – Both material and Device

आवेदन प्रक्रिया / Application Process:

Duly filled application form along with the requested details, scanned copies of certificates, other supporting documents, should be uploaded through the online portal (https://apply.iitjammu.ac.in/#/home) **latest by 04.02.2026.** Please apply through the [contract/project staff/JRF/SRF] tab on the referred application portal. Candidates who are already employed should produce a relieving certificate from their employers, if selected. The interview will be conducted for all shortlisted candidates.

महत्वपूर्ण बिंदु / Important Points:

1. The applicant will be responsible for the authenticity of the information, other documents, and photographs submitted.
2. Merely possessing the prescribed qualification does not ensure that the candidate would be called for an Interview. The candidates may be shortlisted based on merit and need for the project.
3. Shortlisted candidates will be informed by e-mail about the interview. So, the candidate must provide valid e-mail IDs, phone number information in their applications.
4. Shortlisted candidates must present themselves for the interview on the interview date with an updated CV and original and attested photocopies of mark sheets/certificates in support of their academic qualifications. Only shortlisted candidates will be called for the interview. The time of the interview will be informed to the shortlisted candidates by e-mail. The interview will be held by using the online platform.
5. Candidates who are already employed should produce a relieving certificate from their employers, if selected.

6. The last date for receiving the duly filled in application is **04.02.2026** through the online portal.
7. The date of interview will be informed to the shortlisted candidates through email.
8. The selected JRF may get an opportunity to pursue PhD at IIT Jammu as per institute norms subject to their performance evaluation and suitability for PhD program.

पत्राचार का पता / Address for Correspondence:

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